

ABSTRACT OF THE DISCLOSURE

A chemical vapor deposition apparatus includes a deposition chamber defined at least in part by chamber walls, a substrate holder inside the chamber, and at least one process chemical inlet to the chamber. At least one purge inlet to the chamber is positioned elevationally above the substrate holder and outside a lateral periphery of the substrate holder. The purge inlet is configured to inject at least one purge material into the chamber and past the substrate holder. The purge inlet can be positioned and configured to inject an annular purge material curtain concentric to the substrate holder. A chemical vapor deposition method includes injecting at least one purge material into a deposition chamber and forming a purge curtain from the injected purge material. The purge curtain can extend downward from elevationally above a substrate holder and outside a lateral periphery of the substrate holder. The purge curtain can flow past the substrate holder.